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Examiner Initials	Document Number	Kind Code (if known)	Country	Date of Publication (MM-DD-YYYY)	Translation Yes No
an ✓	7-201749		Japan	08-04-1995	<input checked="" type="checkbox"/> <input type="checkbox"/>
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Examiner Initials	Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
BR	Robert C. REID et al. "Lennard-Jones Potentials as Determined from Viscosity Data (Appendix B)", <i>The Properties of Gases and Liquids</i> , McGraw-Hill, Inc., Copyright 1987, p.734, Index
BR	R. Byron BIRD et al. "Diffusivity and the Mechanisms of Mass Transport; Theory of Ordinary Diffusion in Gases at Low Density", <i>Transport Phenomena</i> , John Wiley & Sons, Inc., Copyright 1960, p. 508-513
BR	"Flow of Atoms and Molecules—Rarefied Gas Dynamics and its Applications", section 2.6.4, The Japan Society of Mechanical Engineers, 1996, Kyoritsu Shuppan Co., Ltd.
BR	Shingo KADOMURA et al., "ANISOTROPIC ETCHING USING DEPOSITION OF SULFUR, Sony Corporation, Semiconductor World, January 1993, pp. 1-11, and translation
BR	Ken FUJITA et al., "X-RAY PHOTOELECTRON SPECTROSCOPIC STUDIES ON PYROLYSIS OF PLASMA-POLYMERIZED FLUOROCARBON FILMS ON Si", Jpn. J. Appl. Phys. volume 34 (1995), pp. 304-306, Part 1, NO. 1, January 1995
BR	Riccardo d'AGOSTINO et al., "PLASMA ETCHING OF Si and SiO ₂ in SF ₆ -O ₂ MIXTURES", J. Appl. Phys. 52(1), January 1981, pp. 162-167

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